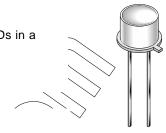
F5E1/2/3 AIGaAs INFRARED EMITTING DIODE

PACKAGE DIMENSIONS 0.209 (5.31) 0.184 (4.67) 0.030 (0.76) 0.155 (3.94) NQM MAX 1.00 (25.4) MIN ANODE (CASE) 0.100 (2.54) 0.050 (1.27) 0.040 (1.02) Ø0.020 (0.51) 2X 0.040 (1.02) NOTES:

- 1. Dimensions for all drawings are in inches (mm).
- 2. Tolerance of \pm .010 (.25) on all non-nominal dimensions unless otherwise specified.

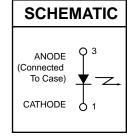
DESCRIPTION

The F5E series are 880nm LEDs in a wide angle, TO-46 package.



FEATURES

- · Good optical to mechanical alignment
- Mechanically and wavelength matched to the TO-18 series phototransistor
- · Hermetically sealed package
- · High irradiance level





- 1. Derate power dissipation linearly 1.70 mW/°C above 25°C ambient.
- 2. Derate power dissipation linearly 13.0 mW/°C above 25°C case.
- 3. RMA flux is recommended.
- 4. Methanol or isopropyl alcohols are recommended as cleaning agents.
- 5. Soldering iron tip 1/16" (1.6mm) minimum from housing.
- 6. As long as leads are not under any stress or spring tension
- $^{\prime}$ 7. Total power output, P_O, is the total power radiated by the device into a solid angle of 2 π steradians.

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise specified)

	* *		
Parameter	Symbol	Rating	Unit
Operating Temperature	T _{OPR}	-65 to +125	°C
Storage Temperature	T _{STG}	-65 to +150	°C
Soldering Temperature (Iron)(3,4,5 and 6)	T _{SOL-I}	240 for 5 sec	°C
Soldering Temperature (Flow)(3,4 and 6)	T _{SOL-F}	260 for 10 sec	°C
Continuous Forward Current	l _F	100	mA
Forward Current (pw, 10µs; 100Hz)	l _F	3	A
Forward Current (pw, 1µs; 200Hz)	l _F	10	A
Reverse Voltage	V _R	3	V
Power Dissipation (T _A = 25°C) ⁽¹⁾	P _D	170	mW
Power Dissipation (T _C = 25°C) ⁽²⁾	P _D	1.3	W

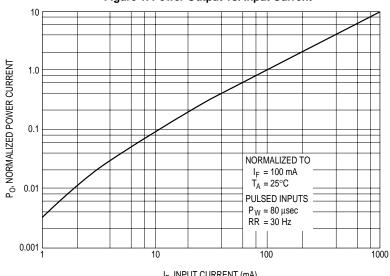
ELECTRICAL / OPTICAL CHARACTERISTICS (TA =25°C) (All measurements made under pulse conditions)

PARAMETER	TEST CONDITIONS	SYMBOL	MIN	TYP	MAX	UNITS
Peak Emission Wavelength	$I_{F} = 100 \text{ mA}$	λ_{PE}	_	880	_	nm
Emission Angle at 1/2 Power		θ	_	±40	_	Deg.
Forward Voltage	I _F = 100 mA	V_{F}	_	_	1.7	V
Reverse Leakage Current	V _R = 3 V	I _R	_	_	10	μA
Total Power F5E1 (7)	I _F = 100 mA	Po	12.0	_	_	mW
Total Power F5E2 (7)	I _F = 100 mA	Po	9.0	_	_	mW
Total Power F5E3 (7)	I _F = 100 mA	Po	10.5	_	_	mW
Rise Time 0-90% of output		t _r	_	1.5	_	μs
Fall Time 100-10% of output		t _f	_	1.5	_	μs

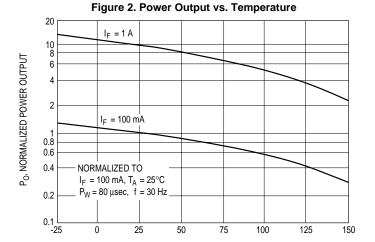


F5E1/2/3 **AIGAAS INFRARED EMITTING DIODE**



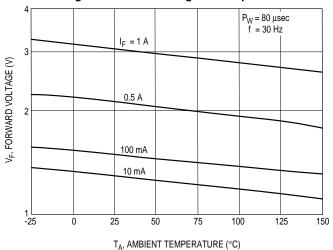


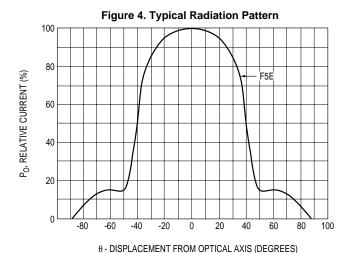
IF, INPUT CURRENT (mA)

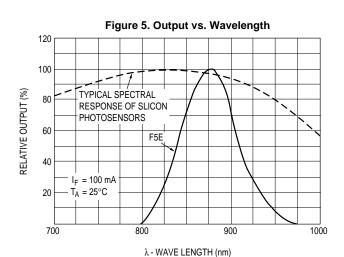


 T_A , AMBIENT TEMPERATURE (°C)











F5E1/2/3 AIGaAs INFRARED EMITTING DIODE

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